



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89 Plastic-Encapsulate Transistors

KTA1666 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.5 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -2 A

Collector-base voltage

$V_{(BR)CBO}$: -50 V

Operating and storage junction temperature range

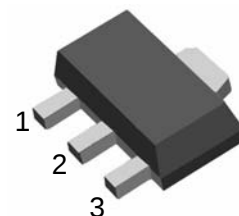
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1mA, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2V, I_C=-500mA$	70		240	
	$h_{FE(2)}$	$V_{CE}=-2V, I_C=-1.5A$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-1A, I_B=-50mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-1A, I_B=-50mA$			-1.2	V
Transition frequency	f_T	$V_{CE}=-2V, I_C=-500mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		40		pF
Switching Time	Turn on Time	t_{on}	$V_{CC}=30V, I_C=1A, I_{B1}=-I_{B2}=-0.05A$	0.1		μs
	Storage Time	t_{stg}		1.0		
	Fall Time	t_f		0.1		

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	70-140	120-240
Marking	WO	WY